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## **ABSTRACT OF THE DISCLOSURE**

A method of fabricating a semiconductor device to prevent contaminating particle formation. The method includes depositing a layer having a selected thickness on a wafer and then planarizing the deposited layer. A photoresist layer is then coated on the deposited layer. An edge portion of the coated photoresist layer is removed to thereby expose a dead zone region of the deposited layer, with the dead zone region corresponding to a portion of the initial deposited layer which is not removed during the planarization process. The exposed deposited layer of the dead zone region is then etched, and the photoresist layer remaining on the wafer is stripped to form the desired pattern.